IDT709279S/L

Features

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 9/12/15ns (max.)
 - Industrial: 12ns (max.)
- Low-power operation
 - IDT709279S

Active: 950mW (typ.) Standby: 5mW (typ.)

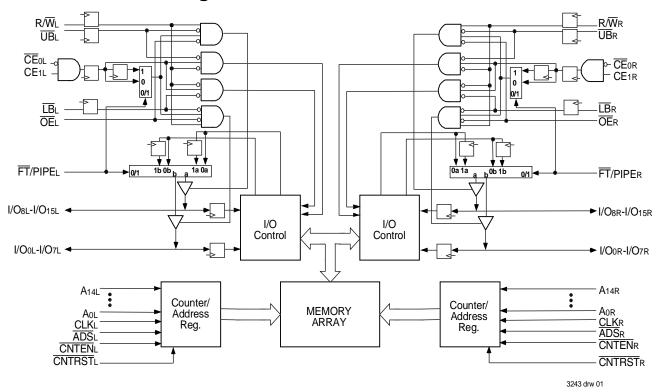
- IDT709279L

Active: 950mW (typ.) Standby: 1mW (typ.)

- Flow-Through or Pipelined output mode on either port via the FT/PIPE pin
- Counter enable and reset features

- Dual chip enables allow for depth expansion without additional logic
- Full synchronous operation on both ports
 - 4ns setup to clock and 1ns hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 9ns clock to data out in the Pipelined output mode
 - Self-timed write allows fast cycle time
 - 15ns cycle time, 66MHz operation in Pipelined output mode
- Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- TTL- compatible, single 5V (±10%) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 100-pin Thin Quad Flatpack (TQFP) package

Functional Block Diagram



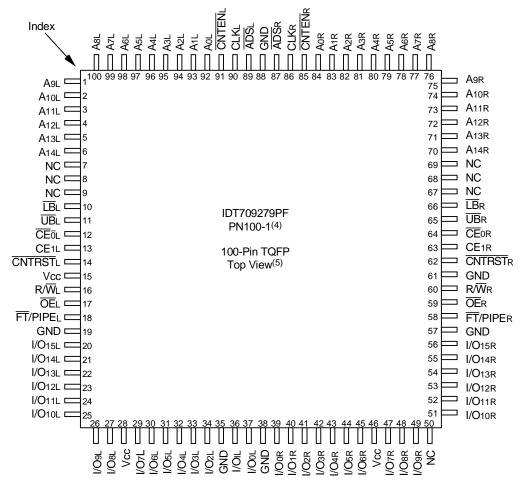
AUGUST 2001

Description

The IDT709279 is a high-speed 32K x 16 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times.

With an input data register, the IDT709279 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{\text{CE}}$ 0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 950mW of power.

Pin Configurations (1,2,3)



NOTES: 3243 drw 02

- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- 3. Package body is approximately 14mm x 14mm x 1.4mm
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names
CEOL, CE1L	Œ0R, CE1R	Chip Enables
R/\overline{W}_L	R/WR	Read/Write Enable
ŌĒL	OE R	Output Enable
A0L - A14L	A0R - A14R	Address
I/Ool - I/O15L	I/O0R - I/O15R	Data Input/Output
CLKL	CLKR	Clock
ŪB∟	Ū B R	Upper Byte Select
<u>LB</u> ∟	<u>∏</u> R	Lower Byte Select
AD S L	ĀD S̄ _R	Address Strobe
CNTENL	<u>CNTEN</u> R	Counter Enable
CNTRSTL	<u>CNTRST</u> _R	Counter Reset
FT/PIPEL FT/PIPER		Flow-Through/Pipeline
V	CC	Power
G	ND	Ground

3243 tbl 01

<u>Truth Table I—Read/Write and Enable Control(1,2,3)</u>

ŌĒ	CLK	Œ	CE ₁	IB	lВ	R/W	Upper Byte I/O8-15	Lower Byte I/O ₀₋₇	Mode
Х	\uparrow	Н	Х	Х	Х	Х	High-Z	High-Z	Deselected—Power Down
Х	\uparrow	Х	L	Χ	Х	Х	High-Z	High-Z	Deselected—Power Down
Х	1	L	Н	Н	Н	Х	High-Z	High-Z	Both Bytes Deselected
Х	1	L	Н	L	Н	L	Din	High-Z	Write to Upper Byte Only
Х	1	L	Н	Н	L	L	High-Z	Din	Write to Lower Byte Only
Х	\uparrow	L	Н	L	L	L	DIN	Din	Write to Both Bytes
L	\uparrow	L	Н	L	Н	Н	D оит	High-Z	Read Upper Byte Only
L	1	L	Н	Н	L	Н	High-Z	Dout	Read Lower Byte Only
L	1	L	Н	L	L	Н	Dоит	Douт	Read Both Bytes
Н	Χ	L	Н	L	L	Χ	High-Z	High-Z	Outputs Disabled

1. "H" = VIH, "L" = VIL, "X" = Don't Care. 2. ADS, CNTEN, CNTRST = X.

3. $\overline{\text{OE}}$ is an asynchronous input signal.

Truth Table II—Address Counter Control^(1,2)

Address	Previous Address	Addr Used	CLK	ADS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
Х	Х	0	1	Х	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to Address 0
An	Х	An	1	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
An	Ар	Ар	↑	Н	Н	Н	Dvo(p)	External Address Blocked—Counter disabled (Ap reused)
Х	Ар	Ap + 1	1	Н	L ⁽⁵⁾	Н	Dvo(p+1)	Counter Enabled—Internal Address generation

NOTES: 3243 tbl 03

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. \overline{CE}_0 , \overline{LB} , \overline{UB} , and \overline{OE} = VIL; CE1 and R/ \overline{W} = VIH.
- 3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.
- 4. \overline{ADS} is independent of all other signals including \overline{CE}_0 , \overline{CE}_1 , \overline{UB} and \overline{LB} .
- 5. The address counter advances if ONTEN = VIL on the rising edge of CLK, regardless of all other signals including CEo, CE1, UB and LB.

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

1. This is the parameter Ta. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	٧
GND	Ground	0	0	0	٧
VIH	Input High Voltage	2.2	_	6.0(1)	V
VIL	Input Low Voltage	-0.5 ⁽²⁾	_	0.8	V

3243 tbl 05

NOTES:

NOTES:

3243 tbl 04

- 1. VTERM must not exceed Vcc + 10%.
- 2. VIL \geq -1.5V for pulse width less than 10ns.

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
Іоит	DC Output Current	50	mA

NOTES:

3243 tbl 06

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

CAPACITANCE⁽¹⁾

$(TA = +25^{\circ}C, f = 1.0MHz)$

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	$V_{IN} = 3dV$	9	pF
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF

- 1. These parameters are determined by device characterization, but are not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references Ci/o.

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range (Vcc = 5.0V ± 10%)

			709279S/L		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
LI	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, $Vin = 0V$ to Vcc	-	10	μΑ
ILO	Output Leakage Current	CE0 = VIH or CE1 = VIL, Vout = 0V to Vcc	ı	10	μA
Vol	Output Low Voltage	IOL = +4mA	ı	0.4	٧
Voh	Output High Voltage	IOH = -4mA	2.4	_	V

NOTE

3243 tbl 08

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁶⁾ ($Vcc = 5V \pm 10\%$)

					70927 Com'l		70927 Cor & I	m'l	70927 Com'l		
Symbol	Parameter	Test Condition	Versio	on	Typ. ⁽⁴⁾	Max.	Тур. ⁽⁴⁾	Max.	Тур. ⁽⁴⁾	Max.	Unit
Icc	Dynamic Operating Current	CEL and CER= VIL Outputs Disabled	COM'L	S L	210 210	390 350	200 200	345 305	190 190	325 285	mA
	(Both Ports Active)	f = fMAX ⁽¹⁾	IND	S L			200 200	380 340			
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CE}_L = \overline{CE}_R = V_{IH}$ $f = f_{IMAX}^{(1)}$	COM'L	S L	50 50	135 115	50 50	110 90	50 50	110 90	mA
	Level inputs)		IND	S L	1 1	1 1	50 50	125 105	1 1		
ISB2	Standby Current (One Port - TTL Level Inputs)	\overline{CE} "A" = VL and \overline{CE} "B" = VH ⁽³⁾	COM'L	S L	140 140	270 240	130 130	230 200	120 120	220 190	mA
	Level inputs)	Active Port Outputs Disabled, f=fMAX ⁽³⁾	IND	S L		11	130 130	245 215	1 1		
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	Both Ports CER and $\overline{CE}_L \ge VCC - 0.2V$ $V\mathbb{N} > VCC - 0.2V$ or	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 5	mA
	Civios Level inpuis)	$VIN \ge VCC - 0.2V OI$ $VIN \le 0.2V, f = 0^{(2)}$	IND	S L			1.0 0.2	15 5			
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	CE"A" ≤ 0.2V and CE"B" ≥ VCC - 0.2V ⁽⁵⁾ VIN > VCC - 0.2V or	COM'L	S L	130 130	245 225	120 120	205 185	110 110	195 175	mA
	TOWOS LEVEL IIIPUIS)	$VIN \ge VCC - 0.2V$ of $VIN \le 0.2V$, Active Port Outputs Disabled, $f = fMAX^{(1)}$	IND	S L	_		120 120	220 200	-		

NOTES:

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. Vcc = 5V, TA = 25°C for Typ, and are not production tested. Icc pc(f=0) = 150mA (Typ).
- 5. $\overline{CE}x = VIL \text{ means } \overline{CE}ox = VIL \text{ and } CE1x = VIH$
 - $\overline{CE}x = VIH means \overline{CE}_0x = VIH or CE_1x = VIL$
 - $\overline{\text{CE}}\text{x} \leq 0.2 \text{V}$ means $\overline{\text{CE}}\text{ox} \leq 0.2 \text{V}$ and $\text{CE}\text{1x} \geq \text{Vcc}$ 0.2 V
 - $\overline{\text{CE}}$ x \geq Vcc 0.2V means $\overline{\text{CE}}$ 0x \geq Vcc 0.2V or CE1x \leq 0.2V
 - "X" represents "L" for left port or "R" for right port.
- 6. 'X' in part numbers indicate power rating (S or L).

^{1.} At $Vcc \le 2.0V$ input leakages are undefined.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

3243 tbl 10

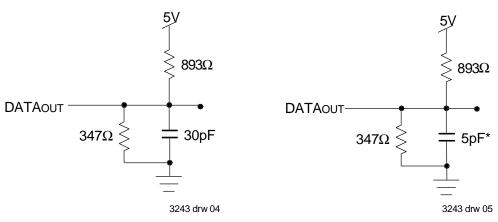


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tcklz, tckHz, tolz, and toHz). *Including scope and jig.

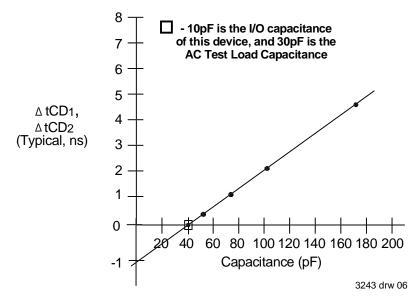


Figure 3. Typical Output Derating (Lumped Capacitive Load).

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(3,4)}$ (Vcc = 5V ± 10%, TA = 0°C to +70°C)

	and Write Cycle 1 iming)(4,47)	709	279X9 'I Only	7092 Co	79X12 om'l Ind	709279X15 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	25	_	30	_	35	_	ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	15	_	20	_	25	_	ns
tcH1	Clock High Time (Flow-Through) ⁽²⁾	12	_	12	_	12	_	ns
tcL1	Clock Low Time (Flow-Through) ⁽²⁾	12	_	12	_	12	_	ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	6	_	8	_	10	_	ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	6	_	8	_	10	_	ns
tr	Clock Rise Time	_	3	_	3	_	3	ns
tF	Clock Fall Time	_	3	_	3	_	3	ns
tsa	Address Setup Time	4	_	4	_	4	_	ns
tha	Address Hold Time	1	_	1	_	1	_	ns
tsc	Chip Enable Setup Time	4	_	4	_	4	_	ns
thc	Chip Enable Hold Time	1	_	1	_	1	_	ns
tsB	Byte Enable Setup Time	4	_	4	_	4	_	ns
tнв	Byte Enable Hold Time	1	_	1	_	1	_	ns
tsw	R/W Setup Time	4	_	4	_	4	_	ns
t _{HW}	R/\overline{W} Hold Time	1	_	1	_	1	_	ns
tsp	Input Data Setup Time	4	_	4	_	4	_	ns
thD	Input Data Hold Time	1	_	1	_	1	_	ns
tsad	ADS Setup Time	4	_	4	_	4	_	ns
thad	ADS Hold Time	1	_	1	_	1	_	ns
tscn	CNTEN Setup Time	4	_	4	_	4	_	ns
thcn	CNTEN Hold Time	1	_	1	_	1	_	ns
tsrst	CNTRST Setup Time	4	_	4	_	4	_	ns
thrst	CNTRST Hold Time	1	_	1	_	1	_	ns
toe	Output Enable to Data Valid	_	12	_	12	_	15	ns
tolz	Output Enable to Output Low-Z ⁽¹⁾	2	_	2	_	2	_	ns
tонz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tcD1	Clock to Data Valid (Flow-Through) ⁽²⁾	_	20	_	25	_	30	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾	_	9	_	12	_	15	ns
toc	Data Output Hold After Clock High	2	_	2	_	2	_	ns
tckhz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2	_	2	_	2	_	ns
Port-to-Port [Delay		•	•	•		•	
tcwdd	Write Port Clock High to Read Data Delay		35	_	40	_	50	ns
tccs	Clock-to-Clock Setup Time	_	15	_	15	_	20	ns

NOTES:

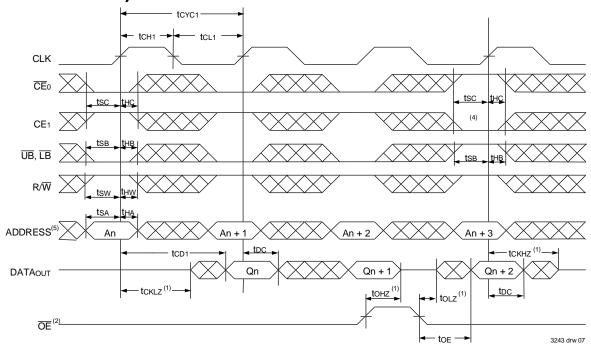
^{1.} Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

^{2.} The Pipelined output parameters (tcyc2, tcb2) apply to either or both left and right ports when FT/PIPE = VIH. Flow-through parameters (tcyc1, tcb1) apply when FT/PIPE = VIL for that port.

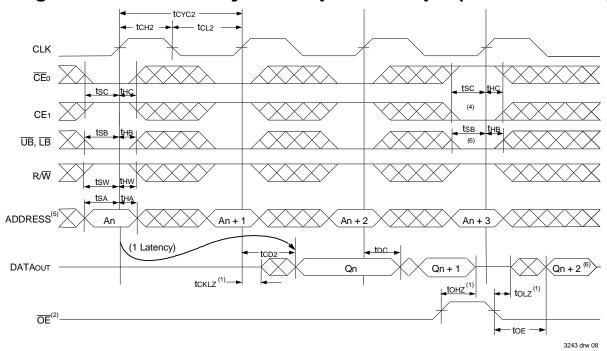
^{3.} All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (\overline{OE}) and $\overline{FT}/PIPE$. $\overline{FT}/PIPE$ should be treated as a DC signal, i.e. steady state during operation.

^{4. &#}x27;X' in part number indicates power rating (S or L).

Timing Waveform of Read Cycle for Flow-Through Output $(\overline{FT}/PIPE"x" = VIL)^{(3,7)}$

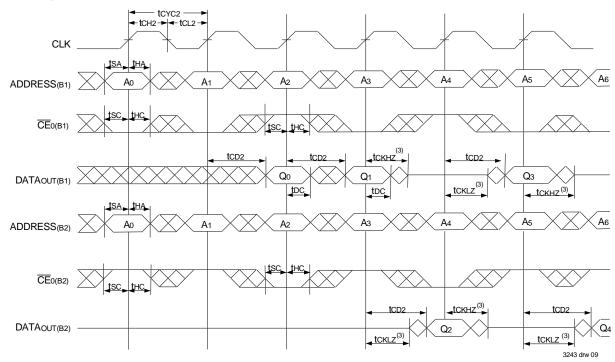


Timing Waveform of Read Cycle for Pipelined Output ($\overline{FT}/PIPE"x" = Vih$)(3,7)

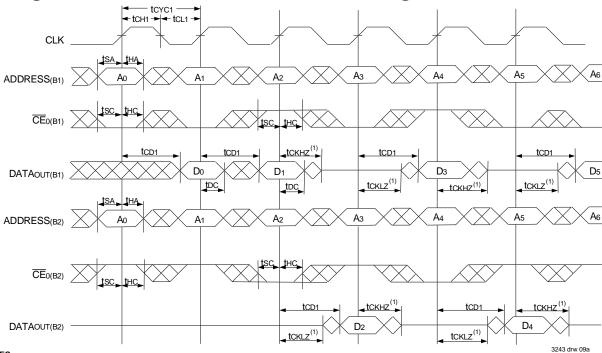


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. $\overline{\text{OE}}$ is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = V_{IL}$, \overline{CNTEN} and $\overline{CNTRST} = V_{IH}$.
- 4. The output is disabled (High-Impedance state) by $\overline{\text{CE}}_0 = \text{V}_{\text{IH}}$, $\overline{\text{CE}}_1 = \text{V}_{\text{IL}}$, $\overline{\text{UB}} = \text{V}_{\text{IH}}$, or $\overline{\text{LB}} = \text{V}_{\text{IH}}$ following the next rising edge of the clock. Refer to Truth Table 1.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers
 are for reference use only.
- 6. If $\overline{\mathsf{UB}}$ or $\overline{\mathsf{LB}}$ was HIGH, then the Upper Byte and/or Lower Byte of DATAoυτ for Qn + 2 would be disabled (High-Impedance state).
- 7. "x" denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read^(1,2)

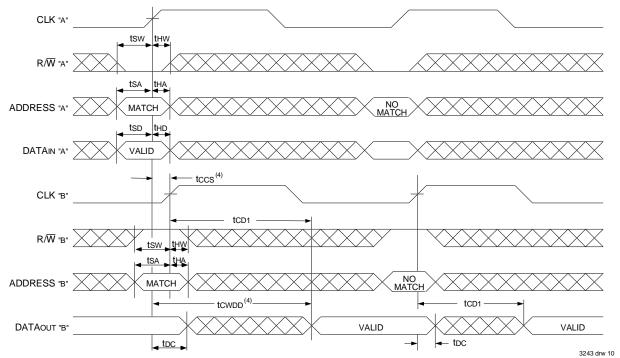


Timing Waveform of a Bank Select Flow-Through Read⁽⁶⁾



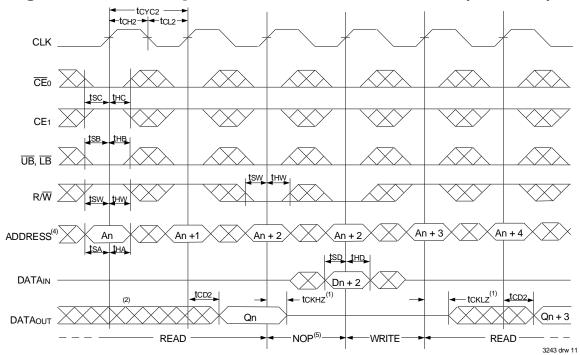
- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT709279 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{UB}}$, $\overline{\text{LB}}$, $\overline{\text{OE}}$, and $\overline{\text{ADS}}$ = VIL; $\overline{\text{CE1(B1)}}$, $\overline{\text{CE1(B2)}}$, $\overline{\text{R/W}}$, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 5. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
- If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwdd.
 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcdl. tcwdd does not apply in this case.

Timing Waveform with Port-to-Port Flow-Through Read^(1,2,3,5)

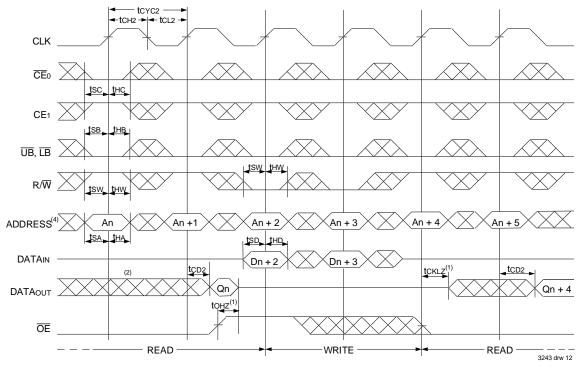


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $\overline{ADS} = VIL$; \overline{CE}_1 , \overline{CNTEN} , and $\overline{CNTRST} = VIH$.
- 3. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 4. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwbb. If tccs > maximum specified, then data from right port READ is not valid until tccs + tcb1. tcwbb does not apply in this case.
- 5. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{\text{OE}}$ = V_IL)⁽³⁾

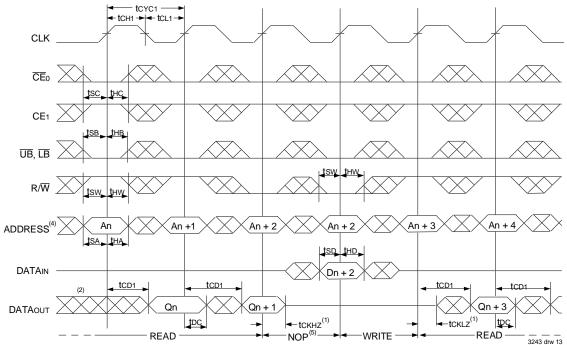


Timing Waveforn of Pipelined Read-to-Write-to-Read (OE Controlled)(3)

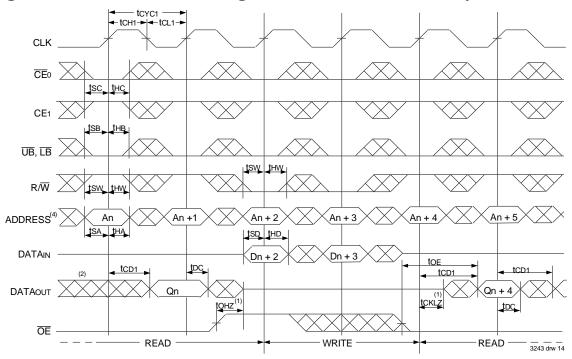


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $\overline{ADS} = V_{IL}$; \overline{CE}_1 , \overline{CNTEN} , and $\overline{CNTRST} = V_{IH}$.
- 4. Addresses do not have to be accessed sequentially since \overline{ADS} = ViL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read $(\overline{OE} = V_{IL})^{(3)}$

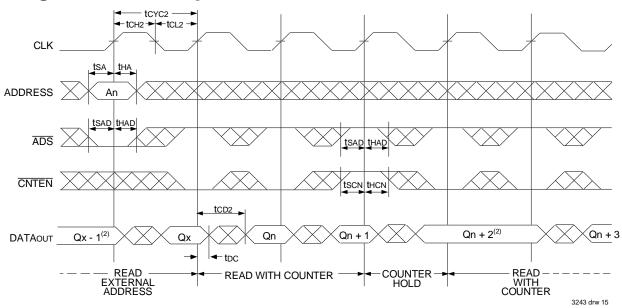


Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{\text{OE}}$ Controlled) $^{(3)}$

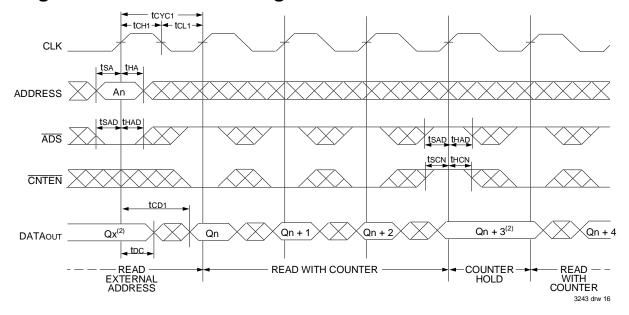


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance is determined by the previous cycle control signals.
- 3. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and $\overline{ADS} = VIL$; $\overline{CE_1}$, \overline{CNTEN} , and $\overline{CNTRST} = VIH$.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

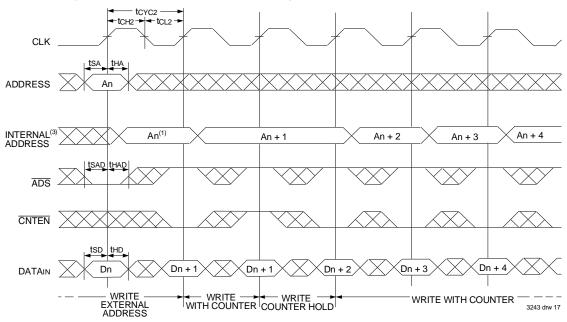


Timing Waveform of Flow-Through Read with Address Counter Advance⁽¹⁾

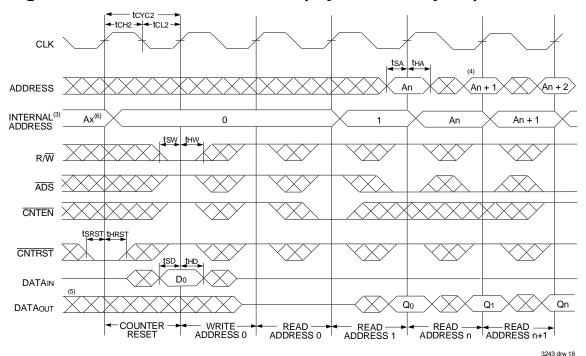


- 1. \overline{CE}_0 , \overline{OE} , \overline{UB} , and \overline{LB} = VIL; CE1, R/ \overline{W} , and \overline{CNTRST} = VIH.
- 2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)(2)



- 1. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{IL}$; CE_1 and $\overline{CNTRST} = V_{IH}$.
- 2. \overline{CE}_0 , \overline{UB} , \overline{LB} = VIL; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when \overline{ADS} = VIL and equals the counter output when \overline{ADS} = VIH.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle. ADDRo will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.

A Functional Description

The IDT709279 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

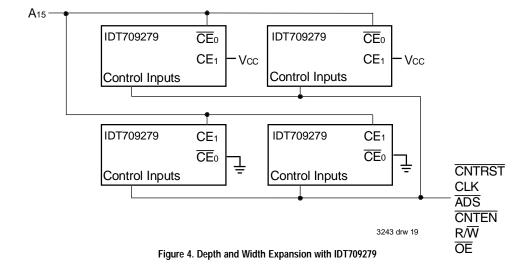
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

A HIGH on $\overline{\text{CE}}_0$ or a LOW on CE₁ for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT709279's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{\text{CE}}_0$ LOW and CE₁ HIGH to reactivate the outputs.

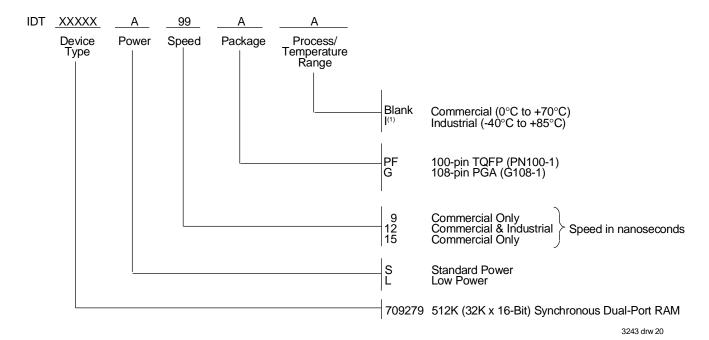
Depth and Width Expansion

The IDT709279 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The 709279 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 32-bit or wider applications.



Ordering Information



NOTES:

1. Industrial temperature range is available.

For specific speeds, packages and powers contact your sales office.

Ordering Information for Flow-through Devices

Old Flow-through Part	New Combined Part
70927S/L20	709279S/L9
70927S/L25	709279S/L12
70927S/L30	709279S/L15

Datasheet Document History

12/9/98: Initiated datasheet document history

Converted to new format

Cosmetic and typographical corrections Added additional notes to pin configurations Pages 13 & 14 Updated timing waveforms

Page 15 Added Depth and Width Expansion section

6/3/99 Changed drawing format

Page 3 Deleted note 6 for Table II

Replaced IDT logo 11/10/99:

3/31/00: Combined Pipelined 709279 family and Flow-through 70927 family offerings into one data sheet

Changed ±200mV in waveform notes to 0mV

Added corresponding part chart with ordering information

5/24/00: Page 1 Inserted diamond in copy

Page 4 Changed information in Truth Table II, Increased storage temperature parameter, clarified TA parameter

Page 5 Changed DC Electrical parameters-changed wording from "Open" to "Disabled"

Page 16 Fixed typeface in heading

Added Industrial Temperature Ranges and removed related notes

8/24/01: Pages 1, 16 and Page Header Removed Preliminary status

Page 5 & 7 Removed Industrial Temperature Ranges for 15ns speed from DC and AC Electrical Characteristics

Page 16 Removed Industrial Temperature from 15ns speed in ordering information